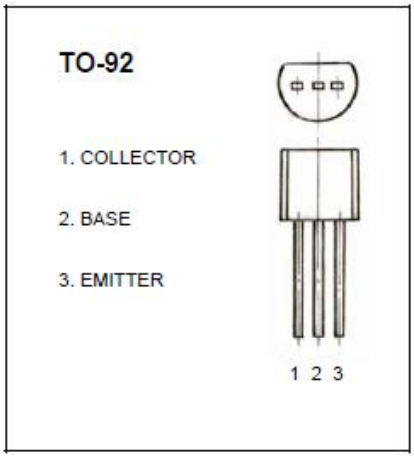
isc Silicon NPN Transistor BC337



DESCRIPTION

- Low Voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- For AF-Driver stages and low power output stages.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	50	V
V_{CEO}	Collector-Emitter Voltage	45	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	800	mA
P_C	Collector Power Dissipation @T_C=25℃	625	mW
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C=100 μ A; I_E= 0	50			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C=10mA; I_B= 0	45			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 100 μ A; I_C= 0	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C=500mA ; I_B= 50mA			0.7	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= 300mA ; V_{CE}= 1V			1.2	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 45V; I_E= 0			0.1	μ A
I_{CEO}	Collector Cutoff Current	V_{CE}= 40V; I_B= 0			0.2	μ A
I_{EBO}	Emitter Cutoff Current	V_{EB}= 4V; I_C= 0			0.1	μ A
h_{FE}	DC Current Gain	I_C=100mA ; V_{CE}= 1V	100		630	
f_T	Current-Gain—Bandwidth Product	I_C= 10mA; V_{CE}= 5V; f= 100MHz	210			MHz

◆ **h_{FE} Classifications**

16	25	40
100-250	160-400	250-630